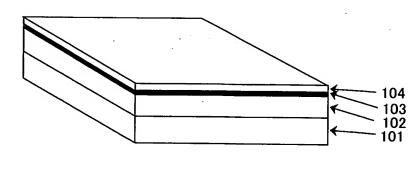
Docket No.: 245402007600

Title: SEMICONDUCTOR LASER DEVICE INCLUDING CLADDING LAYER HAVING STRIPE PORTION DIFFERENT IN CONDUCTIVITY TYPE FROM ADJACENT PORTIONS

FIG.1A



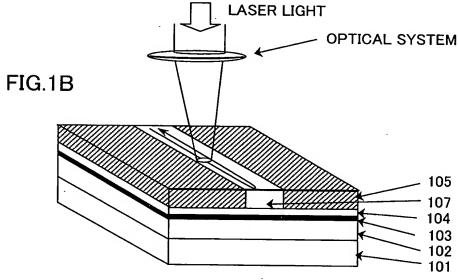
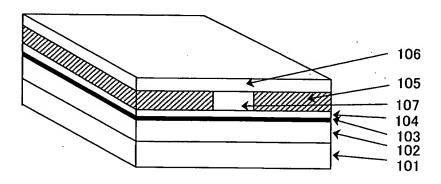


FIG.1C

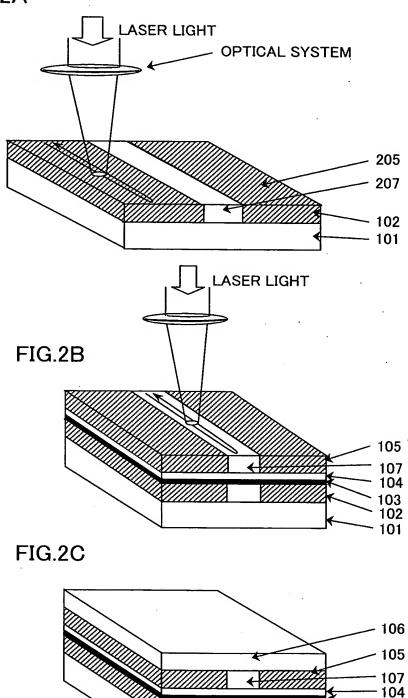


Title: SEMICONDUCTOR LASER DEVICE INCLUDING
CLADDING LAYER HAVING STRIPE PORTION DIFFERENT
IN CONDUCTIVITY TYPE FROM ADJACENT PORTIONS

Docket No.: 245402007600

- 103 - 102 - 101

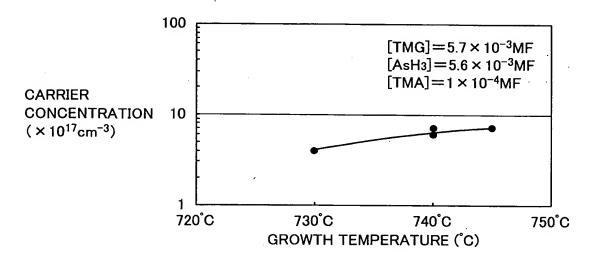
FIG.2A



Title: SEMICONDUCTOR LASER DEVICE INCLUDING
CLADDING LAYER HAVING STRIPE PORTION DIFFERENT
IN CONDUCTIVITY TYPE FROM ADJACENT PORTIONS

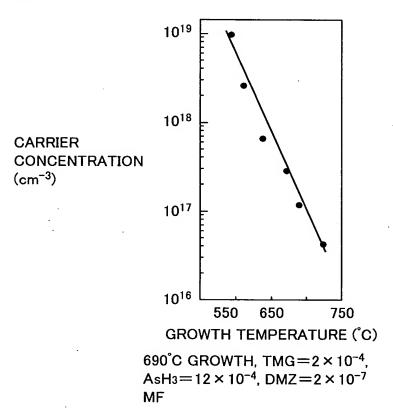
Docket No.: 245402007600

FIG.3



RELATION BETWEEN C DOPE CARRIER CONCENTRATIONS AND CRYSTAL GROWTH TEMPERATURES

FIG.4

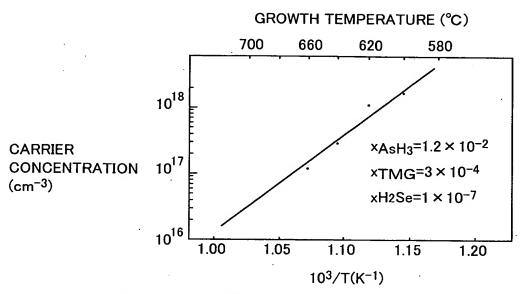


RELATION BETWEEN Zn DOPE CARRIER CONCENTRATIONS AND CRYSTAL GROWTH TEMPERATURES

Title: SEMICONDUCTOR LASER DEVICE INCLUDING
CLADDING LAYER HAVING STRIPE PORTION DIFFERENT
IN CONDUCTIVITY TYPE FROM ADJACENT PORTIONS

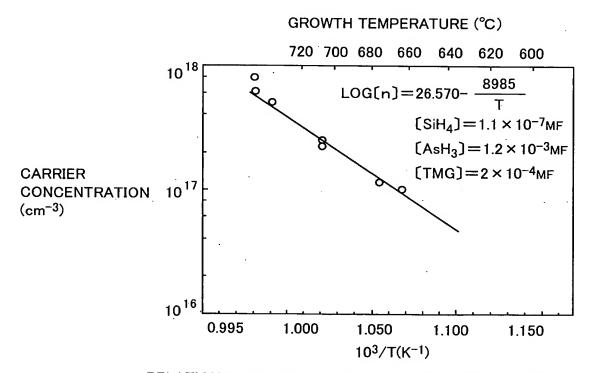
Docket No.: 245402007600

FIG.5



RELATION BETWEEN H2Se DOPE CARRIER CONCENTRATIONS AND CRYSTAL GROWTH TEMPERATURES

FIG.6

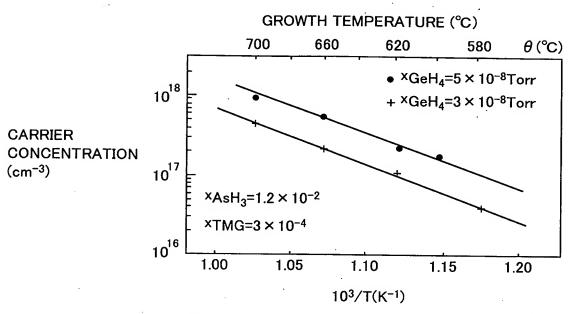


RELATION BETWEEN SiH4 DOPE CARRIER CONCENTRATIONS AND CRYSTAL GROWTH TEMPERATURES

Title: SEMICONDUCTOR LASER DEVICE INCLUDING
CLADDING LAYER HAVING STRIPE PORTION DIFFERENT
IN CONDUCTIVITY TYPE FROM ADJACENT PORTIONS

Docket No.: 245402007600

FIG.7



RELATION BETWEEN GeH4 DOPE CARRIER CONCENTRATIONS AND CRYSTAL GROWTH TEMPERATURES